L Number	Hits	Search Text	DB	Time stamp
1	434		USPAT;	2003/03/27 12:20
		WU-J-Yin. LUR-WATERin. LUR-Win.	US-PGPUB;	
	٠		EPO; JPO;	
			DERWENT;	1.
2	11	//#20020021726#\\ cm /#20020001010#\\ cm	IBM_TDB USPAT:	2002/02/27 12:10
2	11	(("20020031726") or ("20020001919") or ("20030056191") or ("20020025689") or	US-PGPUB;	2003/03/27 12:18
		("20010001191") or ("20020146914")).PN.	EPO; JPO;	
		(20010001191) 01 (20020140914)).FN.	DERWENT;	
			IBM TDB	
3	9294	sti! (shallow adj trench adj isolation)	USPAT;	2003/03/27 12:21
		(0	US-PGPUB;	2000,00,27
4			EPO; JPO;	
			DERWENT;	
			IBM TDB	
4	35565	active adj region	USPAT;	2003/03/27 12:21
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	İ
_	100010		IBM_TDB	
5	106219		USPAT;	2003/03/27 12:22
		si3n4 sixny "si.sub.x n.sub.y"	US-PGPUB;	
			EPO; JPO; DERWENT;	•
			IBM TDB	
6	337	(active adj region) near2 small	USPAT;	2003/03/27 12:22
] 337	(accive day region, nearz smarr	US-PGPUB;	2003,03/21 12:22
			EPO; JPO;	i
			DERWENT;	
			IBM TDB	
7	276	(active adj region) near2 large	USPAT;	2003/03/27 12:22
			US-PGPUB;	
			EPO; JPO;	1
			DERWENT;	
			IBM_TDB	
8	64948	trench	USPAT;	2003/03/27 12:22
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
9	1147369	oxide	IBM_TDB USPAT;	2003/03/27 12:22
	1147505	Oxide	US-PGPUB;	2003/03/27 12:22
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
11	957	hpcvd hdpcvd hdp-cvd	USPAT;	2003/03/27 12:28
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
1.0	1700		IBM_TDB	0000/00/07
12	1788	((high adj density adj plasma) (high adj	USPAT;	2003/03/27 12:30
		density) hdp) adj ((chemical adj vapor adj	US-PGPUB;	
		deposit\$5) cvd)	EPO; JPO;	1
			DERWENT;	
13	36072	 planariz\$5 planaris\$5	IBM_TDB USPAT;	2003/03/27 12:30
	30072	Pranatrato Pranatrato	US-PGPUB;	2003/03/27 12:30
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
14	32913	cmp (((chemical\$3 adj mechanical\$3)	USPAT;	2003/03/27 12:31
		(chemical\$3-mechanical\$3)) adj polish\$3)	US-PGPUB;	
		chemical\$3-mechanical\$3-polish\$3	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
15	4	(("6291111") or ("6178543")).PN.	USPĀT;	2003/03/27 12:33
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	

10	16		USPAT;	2003/03/27 12:41
		photoresist)	US-PGPUB; EPO; JPO; DERWENT;	
16	217	((hpcvd hdpcvd hdp-cvd) (((high adj density adj plasma) (high adj density) hdp) adj ((chemical adj vapor adj deposit\$5) cvd))) with oxide with trench	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/03/27 12:38
17	161	(sti! (shallow adj trench adj isolation)) and (((hpcvd hdpcvd hdp-cvd) (((high adj density adj plasma) (high adj density) hdp) adj ((chemical adj vapor adj	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/03/27 12:38
18	139	deposit\$5) cvd))) with oxide with trench) (sti! (shallow adj trench adj isolation)) and (((hpcvd hdpcvd hdp-cvd)) (((high adj density adj plasma)) (high adj density) hdp) adj ((chemical adj vapor adj deposit\$5) cvd))) with oxide with trench) and (cmp (((chemical\$3 adj mechanical\$3)) (chemical\$3-mechanical\$3)) adj polish\$3) chemical\$3-mechanical\$3-polish\$3)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/27 12:38
19	114	(sti! (shallow adj trench adj isolation)) and (((hpcvd hdpcvd hdp-cvd)) (((high adj density adj plasma) (high adj density) hdp) adj ((chemical adj vapor adj deposit\$5) cvd))) with oxide with trench) and (cmp (((chemical\$3 adj mechanical\$3) (chemical\$3-mechanical\$3)) adj polish\$3) chemical\$3-mechanical\$3-polish\$3) and (silicon adj nitride "si.sub.3 n.sub.4"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/27 12:38
20	100	si3n4 sixny "si.sub.x n.sub.y") (sti! (shallow adj trench adj isolation)) and (((hpcvd hdpcvd hdp-cvd) (((high adj density adj plasma) (high adj density) hdp) adj ((chemical adj vapor adj deposit\$5) cvd))) with oxide with trench) and (cmp (((chemical\$3 adj mechanical\$3) (chemical\$3-mechanical\$3)) adj polish\$3) chemical\$3-mechanical\$3-polish\$3) and (silicon adj nitride "si.sub.3 n.sub.4" si3n4 sixny "si.sub.x n.sub.y") and (resist photoresist mask)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/27 12:40
21	7		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/27 12:41

<u> </u>	0.2		I II C D D M	1 0002 (02 (02 14 02
23	93	((sti! (shallow adj trench adj isolation))	USPAT;	2003/03/27 14:07
		and (((hpcvd hdpcvd hdp-cvd) (((high adj	US-PGPUB;	
		density adj plasma) (high adj density)	EPO; JPO;	
		hdp) adj ((chemical adj vapor adj	DERWENT;	
		deposit\$5) cvd))) with oxide with trench)	IBM_TDB	
		and (cmp (((chemical\$3 adj mechanical\$3)		
		(chemical\$3-mechanical\$3)) adj polish\$3)		
		chemical\$3-mechanical\$3-polish\$3) and		
		(silicon adj nitride "si.sub.3 n.sub.4"		
		si3n4 sixny "si.sub.x n.sub.y") and		
		(resist photoresist mask)) not (((sti!		
		(shallow adj trench adj isolation)) and		
		(((hpcvd hdpcvd hdp-cvd) (((high adj		
		density adj plasma) (high adj density)		
		hdp) adj ((chemical adj vapor adj		
		deposit\$5) cvd))) with oxide with trench)		
		and (cmp (((chemical\$3 adj mechanical\$3)		
		(chemical\$3-mechanical\$3)) adj polish\$3)		
		chemical\$3-mechanical\$3-polish\$3) and		
ļ		(silicon adj nitride "si.sub.3 n.sub.4"		
		si3n4 sixny "si.sub.x n.sub.y") and		
		(resist photoresist mask) and ((active adj		
		region) near2 small) and ((active adj		
		region) near2 large)) (partial adj reverse		
		adj2 (mask active photoresist)))		
25	4	(("6291111") or ("6178543")).PN.	USPAT;	2003/03/27 14:55
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
27	396	oxide with (cmp (((chemical\$3 adj	USPAT	2003/03/27 15:33
		<pre>mechanical\$3) (chemical\$3-mechanical\$3))</pre>		
:		adj polish\$3)		
		chemical\$3-mechanical\$3-polish\$3) with		
		(remov\$3 strip\$4) with etch\$5		
28	42	oxide with (cmp (((chemical\$3 adj	USPAT	2003/03/27 15:45
		mechanical\$3) (chemical\$3-mechanical\$3))		
		adj polish\$3)		
		chemical\$3-mechanical\$3-polish\$3) with		
		(remov\$3 strip\$4) with etch\$5 with (known		
		conventional\$3 typical\$3)		
29	66	oxide with (cmp (((chemical\$3 adj	USPAT	2003/03/27 15:50
		<pre>mechanical\$3) (chemical\$3-mechanical\$3))</pre>		
		adj polish\$3)		
		chemical\$3-mechanical\$3-polish\$3) with		
		(planariz\$5 planaris\$5) with etch\$5 with		
		(known conventional\$3 typical\$3)		
30	20	(oxide with (cmp (((chemical\$3 adj	USPAT	2003/03/27 15:54
ĺ		<pre>mechanical\$3) (chemical\$3-mechanical\$3))</pre>		
		adj polish\$3)		
	1	chemical\$3-mechanical\$3-polish\$3) with		
		(planariz\$5 planaris\$5) with etch\$5 with		
		(known conventional\$3 typical\$3)) and		
	1	(sti! (shallow adj trench adj isolation))		
31	46	(oxide with (cmp (((chemical\$3 adj	USPAT	2003/03/27 15:54
		<pre>mechanical\$3) (chemical\$3-mechanical\$3))</pre>		
		adj polish\$3)		
		chemical\$3-mechanical\$3-polish\$3) with		
		(planariz\$5 planaris\$5) with etch\$5 with		
]	(known conventional\$3 typical\$3)) not		
	1	((oxide with (cmp (((chemical\$3 adj		
]	<pre>mechanical\$3) (chemical\$3-mechanical\$3))</pre>	1	1
	1	adj polish\$3)		
		chemical\$3-mechanical\$3-polish\$3) with		
		chemical\$3-mechanical\$3-polish\$3) with (planariz\$5 planaris\$5) with etch\$5 with		
		chemical\$3-mechanical\$3-polish\$3) with		